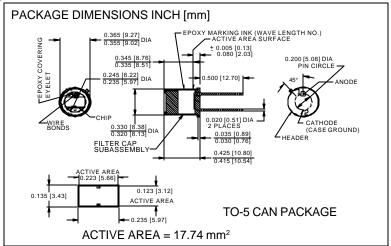
PHOTONIC Silicon Photodiode, Filter Combination Photovoltaic **DETECTORS INC.** (center wavelength 850 nm) Type PDI-V485





FEATURES

- High transmission
- 10⁻⁴ rejection
- +/- 2nm CWL

DESCRIPTION

The PDI-V485 is a silicon, PIN planar diffused, photodiode with a narrow band interferance filter. The detector filter combination has a narrow 10 nm half bandwidth designed for low noise photovoltaic applica-

tions. Packaged in a TO-5 metal can. ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

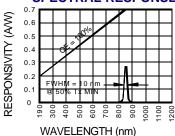
SYMBOL	PARAMETER	MIN	MAX	UNITS	
V_{BR}	Reverse Voltage		100	V	
T _{STG}	Storage Temperature		+85	°C	
То	Operating Temperature Range	-15	+70	°C	
Ts	Soldering Temperature*		+240	°C	
اٍ	Light Current		0.5	mA	

^{*1/16} inch from case for 3 secs max

APPLICATIONS

- Spectrophotometry
- Chemistry instrumentation
- Liquid chromatography

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

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SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS				
lsc	Short Circuit Current***	H = 100 fc, 2850 K	150	200		μΑ				
ΙD	Dark Current	$H = 0, V_R = 10 \text{ mV}$		10	50	pА				
RsH	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$.20	2		GΩ				
TC Rsh	Rsн Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃				
Cı	Junction Capacitance	H = 0, V _R = 10 V**		1700		pF				
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		850		nm				
HBW	Half Bandwidth	(FWHM)		10		nm				
V _{BR}	Breakdown Voltage	I = 10 µuA	50	75		V				
N EP	Noise Equivalent Power	V _R = 10 mV @ Peak		9x10 ⁻¹⁵		W/ √ Hz				
tr	Response Time	RL = 1 KΩ V _R = 10 V		1.0		μS				

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f = 1 MHz, ***without filter [FORM NO. 100-PDI-V485 REV B]